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FIG. 1

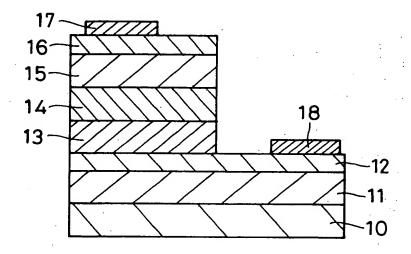
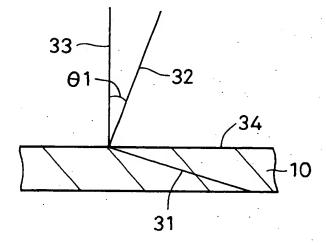


FIG. 2



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FIG.3A

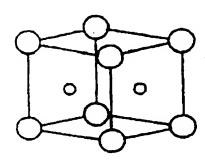
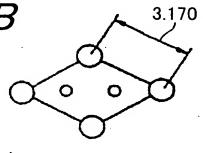


FIG.3B



**o** B

O Zr

FIG.4A

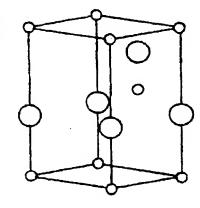
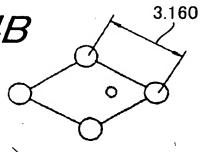


FIG.4B

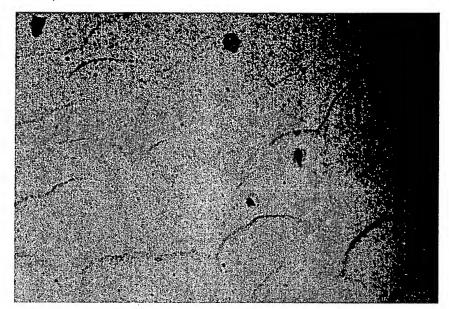


O Ga

O N

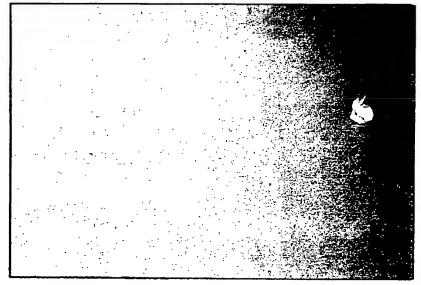
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## FIG. 5



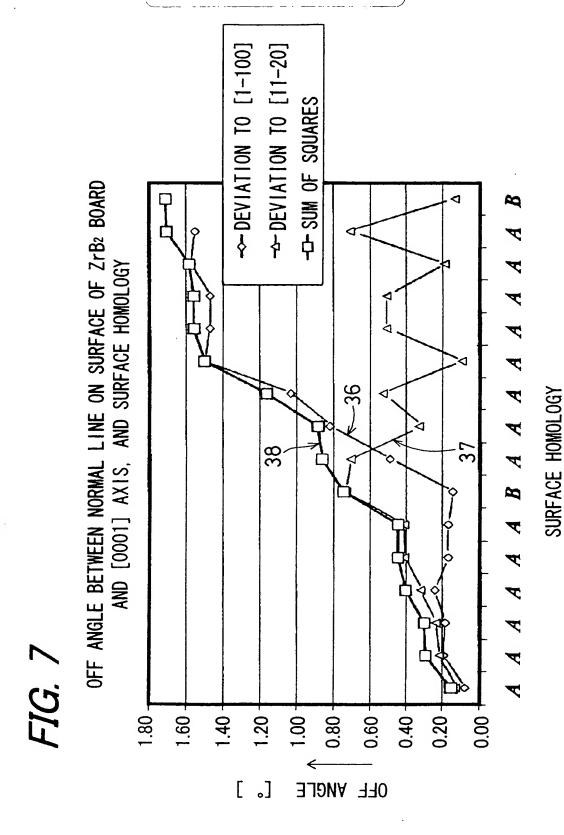
SURFACE STATE B (250  $\mu$  m × 190  $\mu$  m)

#### FIG. 6



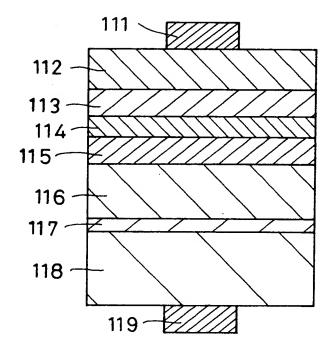
SURFACE STATE A (250  $\mu$  m  $\times$  190  $\mu$  m)

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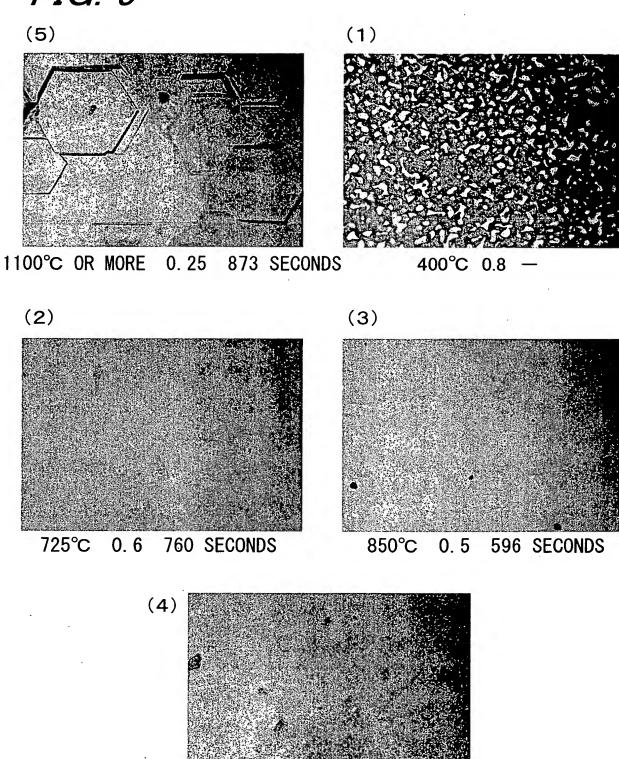
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FIG. 8



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#### FIG. 9



925°C 0.4 -

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FIG. 10

RELATION BETWEEN FILM THICKNESS OF  $(AIN)_x(GaN)_{1-x}$  AND X-RAY HALF VALUE WIDTH

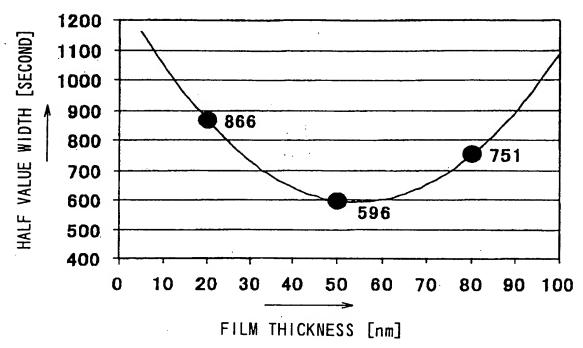


FIG. 11

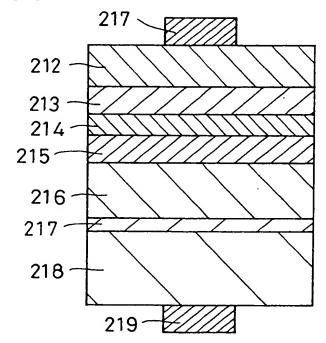
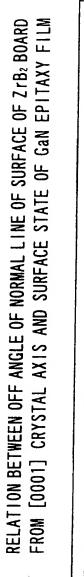
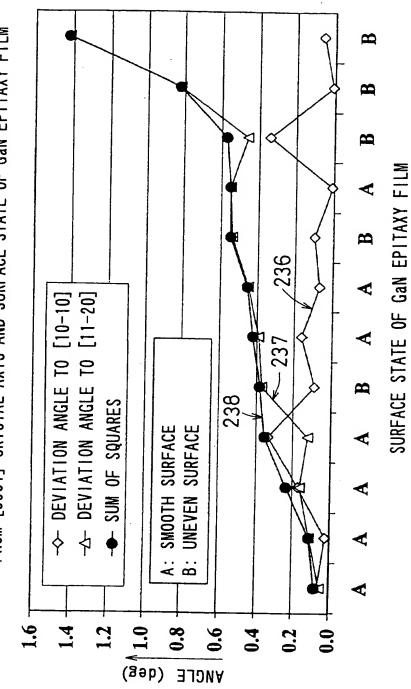


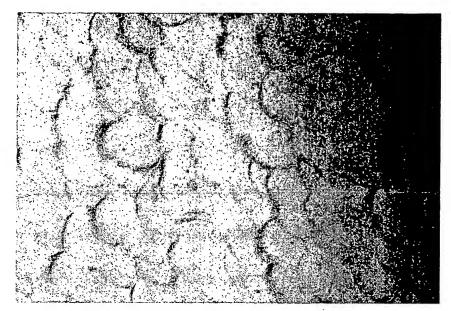
FIG. 12





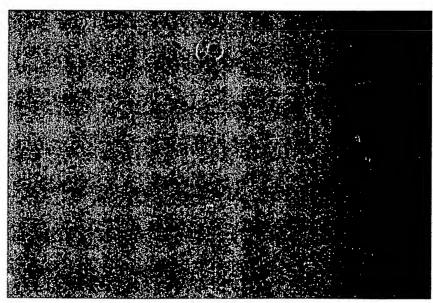
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#### FIG. 13



SURFACE STATE B  $(250 \,\mu\,\text{m} \times 190 \,\mu\,\text{m})$ 

## FIG. 14



SURFACE STATE A  $(250 \,\mu\,\text{m} \times 190 \,\mu\,\text{m})$ 

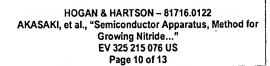


FIG. 15A

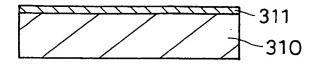


FIG. 15B

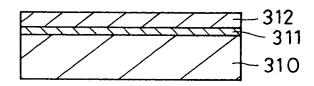


FIG. 15C

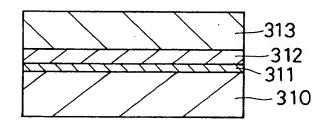


FIG. 15D

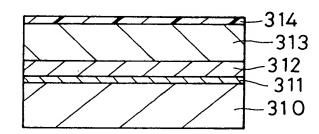


FIG. 15E

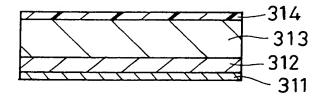
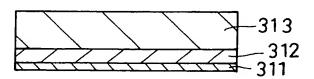
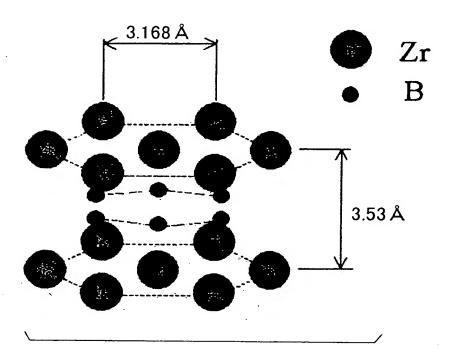


FIG. 15F



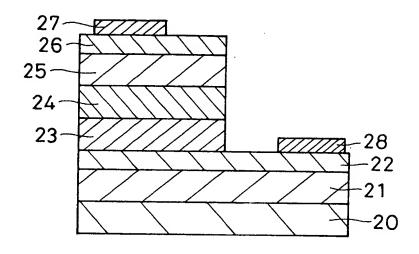
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FIG. 16

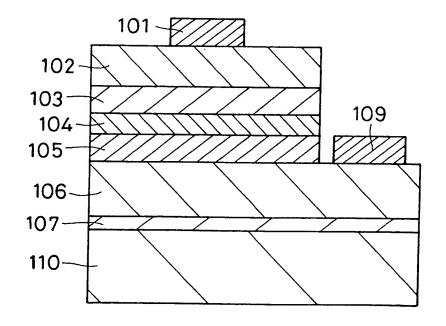


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## FIG. 17 PRIOR ART



#### FIG. 18 PRIOR ART



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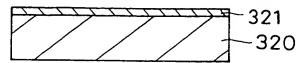


FIG. 19B PRIOR ART

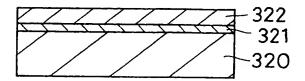


FIG. 19C PRIOR ART

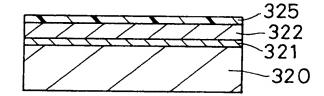


FIG. 19D PRIOR ART

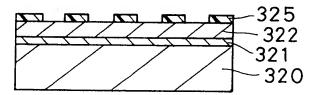


FIG. 19E PRIOR ART

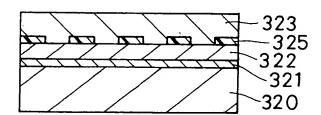


FIG. 19F PRIOR ART

